

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV11** is Designed for Class C, 12.5 Volt operation in FM Amplifier Applications up to 250 MHz.

FEATURES INCLUDE:

- $P_G = 9.0$ dB Typical at 175 MHz
- Emitter Ballasting
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CE}	18 V
V_{CB}	36 V
P_{DISS}	37 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	4.6 $^\circ\text{C/W}$

PACKAGE STYLE .375 4L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B	.785/19.94	
C	.720/18.29	.730/18.54
D	.970/24.64	.980/24.89
E		.385/9.78
F	.004/0.10	.006/0.15
G	.085/2.16	.105/2.67
H	.160/4.06	.180/4.57
I		.280/7.11
J	.240/6.10	.255/6.48

1 = Collector 2 = Base
3 & 4 = Emitter

ORDER CODE: ASI10492

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	36			V
BV_{CES}	$I_C = 50$ mA	36			V
BV_{CEO}	$I_C = 50$ mA	18			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	5.0	50		---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		45		pF
P_G	$V_{CE} = 13.5$ V $P_{OUT} = 15$ W $f = 175$ MHz	8.0	9.0		dB
η_C		60	65		%